

# **NCE60H10**

#### NCE N-Channel Enhancement Mode Power MOSFET

#### **Description**

The NCE60H10 uses advanced trench technology and design to provide excellent R<sub>DS(ON)</sub> with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.

#### **General Features**

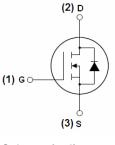
- V<sub>DS</sub> =60V,I<sub>D</sub> =100A  $R_{DS(ON)} < 5.5 \text{ m}\Omega$  @  $V_{GS}=10V$  (Typ:4.8m $\Omega$ )
- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Special designed for convertors and power controls
- Good stability and uniformity with high EAS
- Excellent package for good heat dissipation
- Special process technology for high ESD capability

#### **Application**

- Power switching application
- Hard switched and High frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

100% AVds TESTED!



#### Schematic diagram



Marking and pin assignment



TO-220-3L top view

**Package Marking and Ordering Information** 

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE60H10	NCE60H10	TO-220-3L	-	-	-

## Absolute Maximum Ratings (T<sub>A</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	60	V
Gate-Source Voltage	V <sub>G</sub> S	±20	V
Drain Current-Continuous	I <sub>D</sub>	100	Α
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100℃)	70	Α
Pulsed Drain Current	I <sub>DM</sub>	320	Α
Maximum Power Dissipation	P <sub>D</sub>	170	W
Derating factor		1.13	W/℃
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	812	mJ
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 175	$^{\circ}$



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# Pb Free Product

NCE60H10

Thermal Characteristic			
Thermal Resistance, Junction-to-Case (Note 2)	$R_{ heta JC}$	0.88	°C/W

#### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Parameter Symbol Condition		Min	Тур	Max	Unit
Off Characteristics			•			•
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	V <sub>GS</sub> =0V I <sub>D</sub> =250μA 60		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ , $I_{D}=250\mu A$	2	2.85	4	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	4.8	5.5	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =20A	-	50	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C <sub>lss</sub>	)/ OF)/)/ O)/	-	4900	-	PF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =25V,V <sub>GS</sub> =0V,	-	380	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	290	-	PF
Switching Characteristics (Note 4)			•			•
Turn-on Delay Time	t <sub>d(on)</sub>		-	17	-	nS
Turn-on Rise Time	t <sub>r</sub>	VDD=35V,RL=15Ω	-	11	-	nS
Turn-Off Delay Time	$t_{d(off)}$	RG=2.5Ω,VGS=10V	-	55	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	15	-	nS
Total Gate Charge	Qg	)/ 00\/ L 00 A	-	100	-	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}=30V,I_{D}=20A,$	-	21	-	nC
Gate-Drain Charge	$Q_{gd}$	- V <sub>GS</sub> =10V	-	30	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =20A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	100	Α
Reverse Recovery Time	t <sub>rr</sub>	Tj=25℃,I <sub>F</sub> =100A	-		37	nS
Reverse Recovery Charge	Qrr	di/dt=100A/µs <sup>(Note3)</sup>	-		58	nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

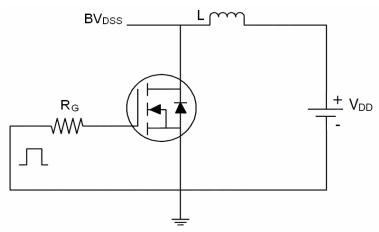
#### Notes:

- $\textbf{1.} \ \textbf{Repetitive Rating: Pulse width limited by maximum junction temperature}.$
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production
- **5.** EAS condition: Tj=25  $^{\circ}\text{C}$  ,VDD=35V,VG=10V,L=0.5mH,Rg=25 $\Omega$

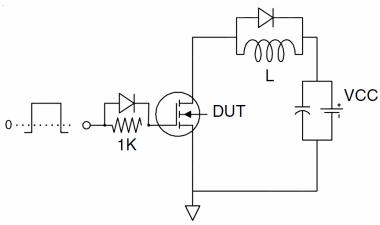


# **Test Circuit**

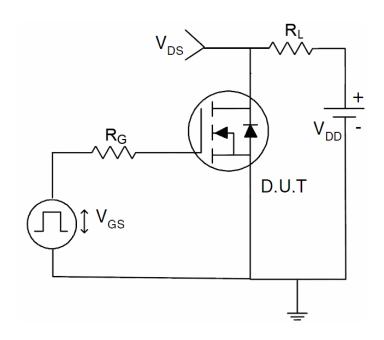
## 1) E<sub>AS</sub> Test Circuits



### 2) Gate Charge Test Circuit

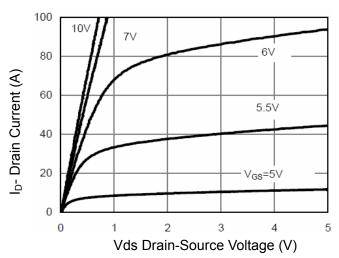


### 3) Switch Time Test Circuit

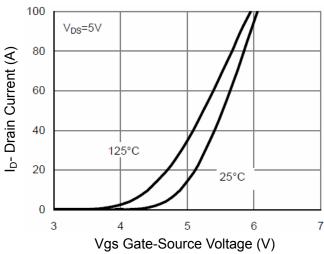




## Typical Electrical and Thermal Characteristics (Curves



**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

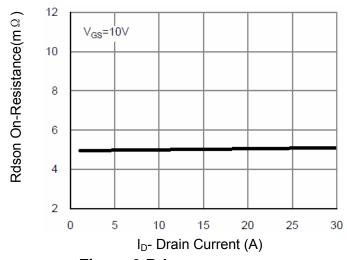
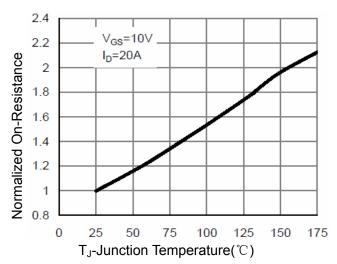


Figure 3 Rdson- Drain Current



**Figure 4 Rdson-Junction Temperature** 

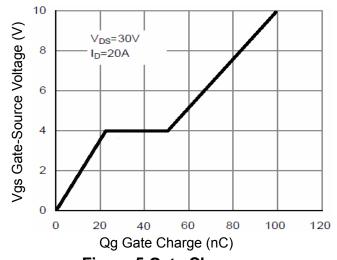


Figure 5 Gate Charge

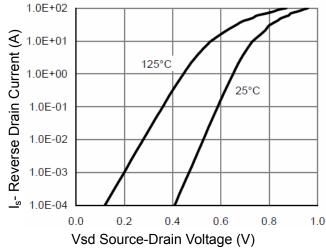
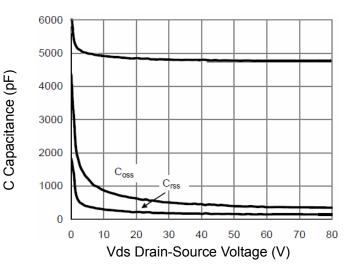
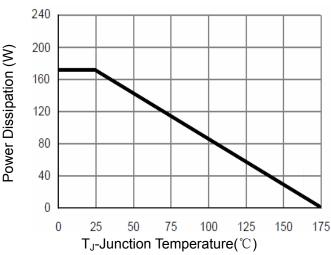
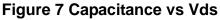


Figure 6 Source- Drain Diode Forward

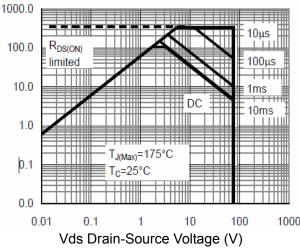


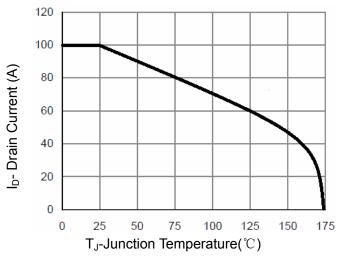












**Figure 8 Safe Operation Area** 

Figure 10 I<sub>D</sub> Current De-rating

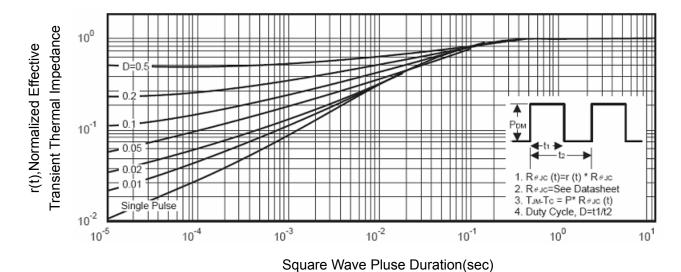
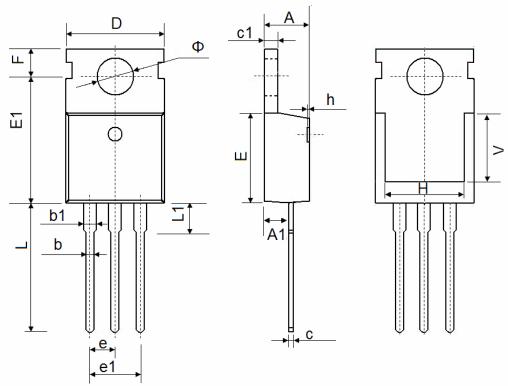


Figure 11 Normalized Maximum Transient Thermal Impedance



# **TO-220-3L Package Information**



Symbol	Dimensions	In Millimeters	Dimensions In Inches		
	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
E	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540	TYP.	0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	7.500 REF.		0.295 REF.		
Ф	3.400	3.800	0.134	0.150	



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